

Kindly enter the following amendments:

IN THE CLAIMS:

Please cancel claims 1-9, 15, 21 and 27 without prejudice or disclaimer of the subject matter thereof.

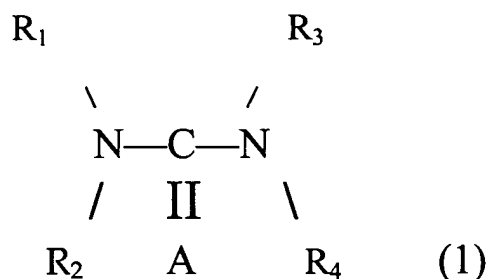
Please amend claims 10-14, 16-20 and 22-26 as follows:

10. (Once Amended) A stripping method which comprises stripping a resist film and/or an etching residue on a semiconductor wafer having an exposed metal film, by using a stripper composition [according to Claim 2] containing an anticorrosive agent which contains (a) urea or a urea derivative, (b) a hydroxy aromatic compound, (c) a hydroxylamine or an alkanolamine, (d) water and (e) a water soluble organic solvent selected from the group including sulfoxides, dimethylformamides, dimethyl acetamides, glycols, glycol ethers, pyrrolidones, imidazolidinones as essential components.

11. (Once Amended) A stripping method which comprises stripping a resist film and/or an etching residue on a semiconductor wafer having an exposed metal film, by using a stripper composition [according to Claim 3] containing an anticorrosive agent which contains (a) urea or a urea derivative, (b) a hydroxy aromatic compound, (c) a hydroxylamine or an alkanolamine, (d) water and (e) a water soluble organic solvent selected from the group including sulfoxides, dimethylformamides, dimethyl acetamides, glycols, glycol ethers, pyrrolidones, imidazolidinones as essential components,  
wherein the amounts of the components (a), (b), (c) and (d) are 1 to 60% by mass, 0.1 to 20% by mass, 5 to 70% by mass and 2 to 40% by mass, respectively.

12. (Once Amended) A stripping method which comprises stripping a resist film and/or an etching residue on a semiconductor wafer having an exposed metal film, by using a stripper composition [according to Claim 4] containing an anticorrosive agent which contains (a) urea or a urea derivative, (b) a hydroxy aromatic compound, and a water soluble organic solvent selected from the group including sulfoxides, dimethylformamides, dimethyl acetamides, glycols, glycol ethers, pyrrolidones, imidazolidinones, as essential components,

wherein the component (a) is a compound represented by the following general formula (1):



(R<sub>1</sub>, R<sub>2</sub>, R<sub>3</sub> and R<sub>4</sub> are each independently a hydrogen atom or an alkyl group having 1 to 3 carbon atoms; and A is an oxygen atom or a sulfur atom).

13. (Once Amended) A stripping method which comprises stripping a resist film and/or an etching residue on a semiconductor wafer having an exposed metal film, by using a stripper composition [according to Claim 5] containing an anticorrosive agent which contains (a) urea or a urea derivative, (b) a hydroxy aromatic compound, having a benzene derivative having at least two phenolic hydroxyl groups in the molecule, and a water soluble organic solvent selected from the group including sulfoxides, dimethylformamides, dimethyl acetamides, glycols, glycol ethers, pyrrolidones, imidazolidinones as essential components.

14. (Once Amended) A stripping method which comprises stripping a resist film and/or an etching residue on a semiconductor wafer having an exposed metal film, by using a stripper composition [according to Claim 6] containing an anticorrosive agent which contains (a) urea or a urea derivative, (b) a hydroxy aromatic compound, and a water soluble organic solvent selected from the group including sulfoxides, dimethylformamides, dimethyl acetamides, glycols, glycol ethers, pyrrolidones, imidazolidinones, as essential components,

wherein the component (b) is a benzene derivative having at least two phenolic hydroxyl groups in the molecule having at least one compound selected from the group consisting of pyrogallol, hydroxyhydroquinone, fluoroglucinol, gallic acid and tannic acid.

16. (Once Amended) A stripping method which comprises:  
forming, on a semiconductor wafer, a metal film and an insulating film in this order;  
forming a resist film thereon;  
conducting dry etching with the resist film being used as a mask, to form, in the insulating film, dents reaching the metal film; then  
stripping the resist film and/or the residue of etching by using a stripper composition [according to Claim 2] containing an anticorrosive agent which contains (a) urea or a urea derivative, (b) a hydroxy aromatic compound, (c) a hydroxylamine or an alkanolamine, (d) water, and (e) a water soluble organic solvent selected from the group including sulfoxides, dimethylformamides, dimethyl acetamides, glycols, glycol ethers, pyrrolidones, imidazolidinones, as essential components.

17. (Once Amended) A stripping method which comprises:

forming, on a semiconductor wafer, a metal film and an insulating film in this order;

forming a resist film thereon;

conducting dry etching with the resist film being used as a mask, to form, in the insulating film, dents reaching the metal film; then

stripping the resist film and/or the residue of etching by using a stripper composition [according to Claim 3] containing an anticorrosive agent which contains (a) urea or a urea derivative, (b) a hydroxy aromatic compound, (c) a hydroxylamine or an alkanolamine, (d) water, and (e) a water soluble organic solvent selected from the group including sulfoxides, dimethylformamides, dimethyl acetamides, glycols, glycol ethers, pyrrolidones, imidazolidinones, as essential components,

wherein the amounts of the components (a), (b), (c) and (d) are 1 to 60% by mass, 0.1 to 20% by mass, 5 to 70% by mass and 2 to 40% by mass, respectively.

18. (Once Amended) A stripping method which comprises:

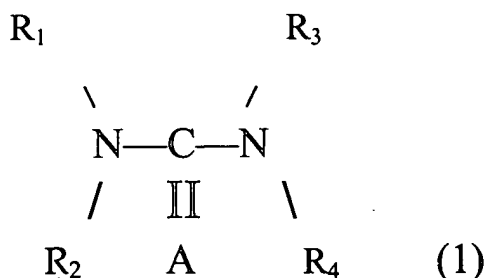
forming, on a semiconductor wafer, a metal film and an insulating film in this order;

forming a resist film thereon;

conducting dry etching with the resist film being used as a mask, to form, in the insulating film, dents reaching the metal film; then

stripping the resist film and/or the residue of etching by using a stripper composition [according to Claim 4] containing an anticorrosive agent which contains (a) urea or a urea derivative, (b) a hydroxy aromatic compound, and a water soluble organic solvent selected from the group including sulfoxides, dimethylformamides, dimethyl acetamides, glycols, glycol ethers, pyrrolidones, imidazolidinones as essential components,

wherein the component (a) is a compound represented by the following general formula (1):



(R<sub>1</sub>, R<sub>2</sub>, R<sub>3</sub> and R<sub>4</sub> are each independently a hydrogen atom or an alkyl group having 1 to 3 carbon atoms; and A is an oxygen atom or a sulfur atom).

19. (Once Amended) A stripping method which comprises:

forming, on a semiconductor wafer, a metal film and an insulating film in this order;

forming a resist film thereon;

conducting dry etching with the resist film being used as a mask, to form, in the insulating film, dents reaching the metal film; then

stripping the resist film and/or the residue of etching by using a stripper composition [according to Claim 5] containing an anticorrosive agent which contains (a) urea or a urea derivative and (b) a hydroxy aromatic compound, having a benzene derivative having at least two phenolic hydroxyl groups in the molecule, and a water soluble organic solvent selected from the group including sulfoxides, dimethylformamides, dimethyl acetamides, glycols, glycol ethers, pyrrolidones, imidazolidinones, as essential components.



20. (Once Amended) A stripping method which comprises:

forming, on a semiconductor wafer, a metal film and an insulating film in this order;

forming a resist film thereon;

conducting dry etching with the resist film being used as a mask, to form, in the insulating film, dents reaching the metal film; then

stripping the resist film and/or the residue of etching by using a stripper composition [according to Claim 6] containing an anticorrosive agent which contains (a) urea or a urea derivative, (b) a hydroxy aromatic compound, and a water soluble organic solvent selected from the group including sulfoxides, dimethylformamides, dimethyl acetamides, glycols, glycol ethers, pyrrolidones, imidazolidinones, as essential components,

wherein the component (b) is a benzene derivative having at least two phenolic hydroxyl groups in the molecule having at least one compound selected from the group consisting of pyrogallol, hydroxyhydroquinone, fluoroglucinol, gallic acid and tannic acid.

22. (Once Amended) A stripping method which comprises:

forming, on a semiconductor wafer, a metal film, a first insulating film and a second insulating film having desired openings;

conducting dry etching with the second insulating film being used as a mask, to form, in the first insulating film, dents reaching the metal film; then

stripping the residue of etching by using a stripper composition [according to Claim 2] containing an anticorrosive agent which contains (a) urea or a urea derivative, (b) a hydroxy aromatic compound, (c) a hydroxylamine or an alkanolamine, (d) water and (e) a water soluble organic solvent selected from the group including sulfoxides, dimethylformamides, dimethyl acetamides, glycols, glycol ethers, pyrrolidones, imidazolidinones as essential components.

23. (Once Amended) A stripping method which comprises:

forming, on a semiconductor wafer, a metal film, a first insulating film and a second insulating film having desired openings;

conducting dry etching with the second insulating film being used as a mask, to form, in the first insulating film, dents reaching the metal film; then

stripping the residue of etching by using a stripper composition [according to Claim 3] containing an anticorrosive agent which contains (a) urea or a urea derivative, (b) a hydroxy aromatic compound, (c) a hydroxylamine or an alkanolamine, (d) water and (e) a water soluble organic solvent selected from the group including sulfoxides, dimethylformamides, dimethyl acetamides, glycols, glycol ethers, pyrrolidones, imidazolidinones as essential components,

wherein the amounts of the components (a), (b), (c) and (d) are 1 to 60% by mass, 0.1 to 20% by mass, 5 to 70% by mass and 2 to 40% by mass, respectively.

24. (Once Amended) A stripping method which comprises:

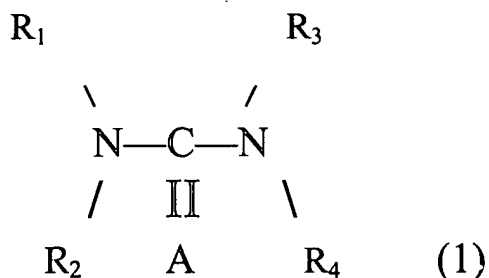
forming, on a semiconductor wafer, a metal film, a first insulating film and a second insulating film having desired openings;

conducting dry etching with the second insulating film being used as a mask, to form, in the first insulating film, dents reaching the metal film; then

stripping the residue of etching by using a stripper composition [according to Claim 4]

containing an anticorrosive agent which contains (a) urea or a urea derivative, (b) a hydroxy aromatic compound, and a water soluble organic solvent selected from the group including sulfoxides, dimethylformamides, dimethyl acetamides, glycols, glycol ethers, pyrrolidones, imidazolidinones, as essential components,

wherein the component (a) is a compound represented by the following general formula (1):



(R<sub>1</sub>, R<sub>2</sub>, R<sub>3</sub> and R<sub>4</sub> are each independently a hydrogen atom or an alkyl group having 1 to 3 carbon atoms; and A is an oxygen atom or a sulfur atom).

25. (Once Amended) A stripping method which comprises:

forming, on a semiconductor wafer, a metal film, a first insulating film and a second insulating film having desired openings;

conducting dry etching with the second insulating film being used as a mask, to form, in the first insulating film, dents reaching the metal film; then

stripping the residue of etching by using a stripper composition [according to Claim 5] containing an anticorrosive agent which contains (a) urea or a urea derivative and (b) a hydroxy aromatic compound, having a benzene derivative having at least two phenolic hydroxyl groups in the molecule, and a water soluble organic solvent selected from the group including sulfoxides, dimethylformamides, dimethyl acetamides, glycols, glycol ethers, pyrrolidones, imidazolidinones, as essential components.

26. (Once Amended) A stripping method which comprises:

forming, on a semiconductor wafer, a metal film, a first insulating film and a second insulating film having desired openings;

conducting dry etching with the second insulating film being used as a mask, to form, in the first insulating film, dents reaching the metal film; then

stripping the residue of etching by using a stripper composition [according to Claim 6] containing an anticorrosive agent which contains (a) urea or a urea derivative, (b) a hydroxy aromatic compound, and a water soluble organic solvent selected from the group including sulfoxides, dimethylformamides, dimethyl acetamides, glycols, glycol ethers, pyrrolidones, imidazolidinones as essential components,

wherein the component (b) is a benzene derivative having at least two phenolic hydroxyl groups in the molecule having at least one compound selected from the group consisting of pyrogallol, hydroxyhydroquinone, fluoroglucinol, gallic acid and tannic acid.